## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

## **Listing of Claims:**

Claims 1-46 (Canceled)

Claim 47 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is integrally formed with said one of the interconnection elements.

Claim 48 (Previously presented): The semiconductor die of claim 67, wherein said one of the interconnection elements comprises a buckling beam interconnection element.

Claim 49 (Previously presented): The semiconductor die of claim 67, wherein said one of the interconnection elements is resilient.

Claims 50-52 (Canceled)

Claim 53 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises at least one of palladium, cobalt, rhodium, tungsten, or diamond.

Claim 54 (Previously presented): The semiconductor die of claim 67, wherein said tip structure comprises a material comprising a spring alloy.

Claim 55 (Previously presented): The semiconductor die of claim 67, wherein said tip structure is secured to said one of the interconnection elements by one of braze or solder.

Claims 56-59 (Canceled)

Claim 60 (Currently amended): A semiconductor die tested by making temporary electrical connections between interconnection elements of a contactor device and terminals of the die, the method of making the temporary electrical connections comprising:

forcing into contact ones of the terminals and blades of ones of the interconnection elements, each blade comprising a cutting edge along a length of the blade,

the blades deflecting across the terminals in a motion that is within plus or minus fortyfive degrees of an axis eorresponding to aligned with the length of the blade, the cutting edge of each blade slicing into a surface of one of the terminals and thereby creating so that a slice mark is created on the one of the terminals.

Claim 61 (Currently amended): The semiconductor die of claim 60, wherein the deflecting motion is within plus or minus thirty degrees of the axis-corresponding to the length of the blade.

Claim 62 (Currently amended): The semiconductor die of claim 60, wherein the deflecting motion is approximately parallel to the axis-corresponding to the length of the blade.

Claim 63 (Previously presented): The semiconductor die of claim 60, wherein the blades slice through oxide layers formed on the terminals.

Claims 64-66 (Canceled)

Claim 67 (Previously presented): The semiconductor die of claim 60, wherein each of the blades composes a tip structure disposed on one of the interconnection elements.

Claims 68 and 69 (Canceled)

Claim 70 (Previously presented): The semiconductor die of claim 60, wherein each of the blades comprises tapered portions that form the cutting edge along the length of the blade.

Claim 71 (Previously presented): The semiconductor die of claim 60, wherein each of the blades comprises a base portion that is larger than the cutting edge of the blade, the blade further comprising tapered sidewalls that taper from the base portion to the cutting edge.

Claim 72 (New): The semiconductor die of claim 60, wherein the axis is coincident with the length of the blade.